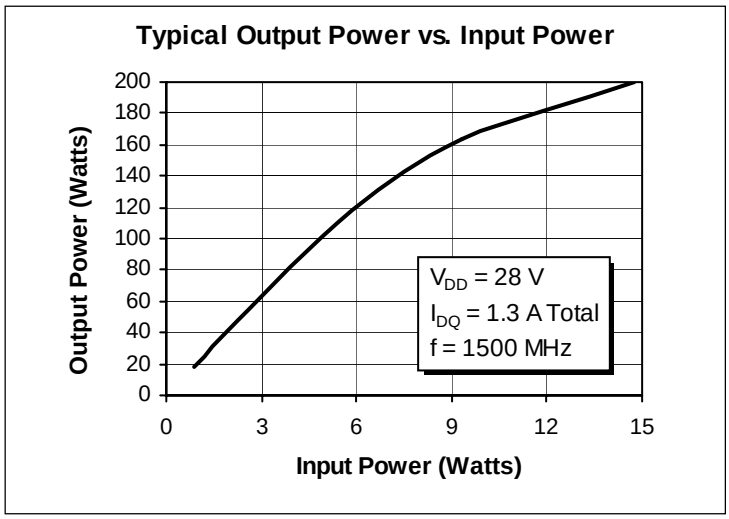
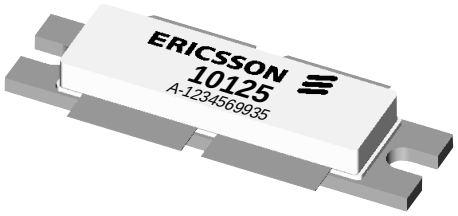
PTF 10125
135 Watts, 1.4–1.6 GHz
GOLDMOS Field Effect Transistor

Description

The PTF 10125 is an internally matched 135–watt *GOLDMOS* FET intended for linear driver and final applications from 1.4 to 1.6 GHz such as DAB/DRB. It operates at 40% efficiency with 12.5 dB typical gain. Nitride surface passivation and full gold metallization ensure excellent device lifetime and reliability.

- ***INTERNALLY MATCHED***
- **Performance at 1.5 GHz, 28 V**
  - Output Power = 135 Watts Min
  - Power Gain = 12.5 dB Typ
- **Full Gold Metallization**
- **Silicon Nitride Passivated**
- **Back Side Common Source**
- **Excellent Thermal Stability**
- **100% Lot Traceability**





Package 20250

RF Specifications (100% Tested)

Characteristic	Symbol	Min	Typ	Max	Units
Gain (V_{DD} = 28 V, P_{OUT} = 30 W, I_{DQ} = 1.3 A Total, f = 1.50, 1.55 GHz)	G_{ps}	11.5	12.5	—	dB
Power Output at 1 dB Compression (V_{DD} = 28 V, I_{DQ} = 1.3 A Total, f = 1.50, 1.55 GHz)	P-1dB	135	150	—	Watts
Drain Efficiency (V_{DD} = 28 V, P_{OUT} = 135 W, I_{DQ} = 1.3 A Total, f = 1.5 GHz)	η_D	35	40	—	%
Load Mismatch Tolerance (V_{DD} = 28 V, P_{OUT} = 67.5 W, I_{DQ} = 1.3 A Total, f = 1.5 GHz —all phase angles at frequency of test)	Ψ	—	—	10:1	—

All published data at T_{CASE} = 25°C unless otherwise indicated.

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Electrical Characteristics (100% Tested—characteristics, conditions and limits shown per side)

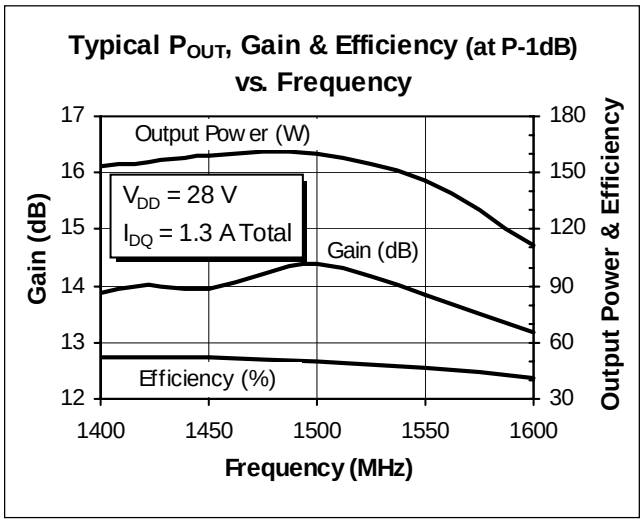
Characteristic	Conditions	Symbol	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 100 mA	$V_{(BR)DSS}$	65	—	—	Volts
Zero Gate Voltage Drain Current	V_{DS} = 28 V, V_{GS} = 0 V	I_{DSS}	—	—	5.0	mA
Gate Threshold Voltage	V_{DS} = 10 V, I_D = 150 mA	$V_{GS(th)}$	3.0	—	5.0	Volts
Forward Transconductance	V_{DS} = 10 V, I_D = 6 A	g_{fs}	2.0	4.0	—	Siemens

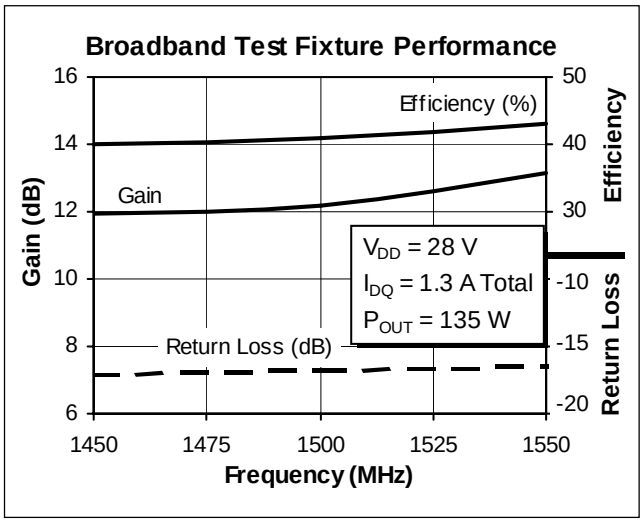
Maximum Ratings

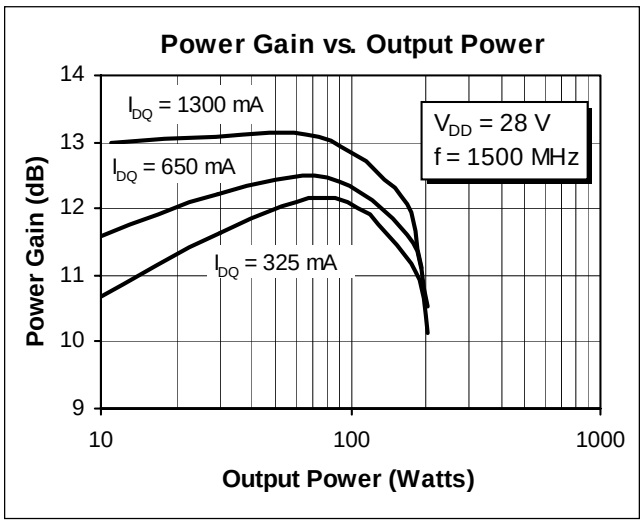
Parameter	Symbol	Value	Unit
Drain-Source Voltage (1)	V_{DSS}	65	Vdc
Gate-Source Voltage (1)	V_{GS}	±20	Vdc
Operating Junction Temperature	T_J	200	°C
Total Device Dissipation Above 25°C derate by	P_D	440 2.51	Watts W/°C
Storage Temperature Range	T_{STG}	–40 to +150	°C
Thermal Resistance (T_{CASE} = 70°C)	$R_{\theta JC}$	0.39	°C/W

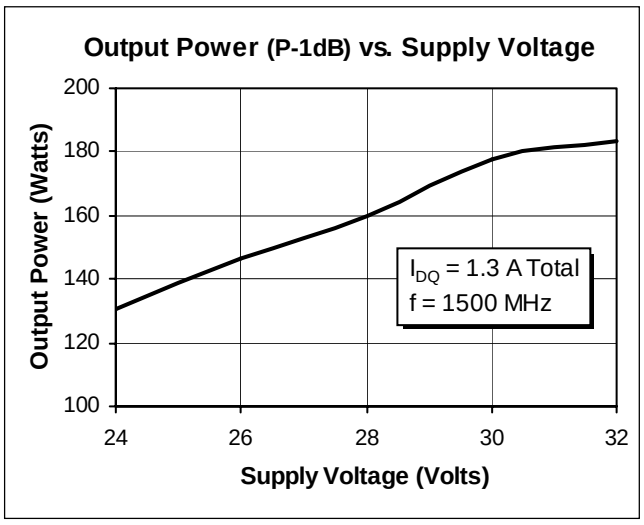
(1)per side

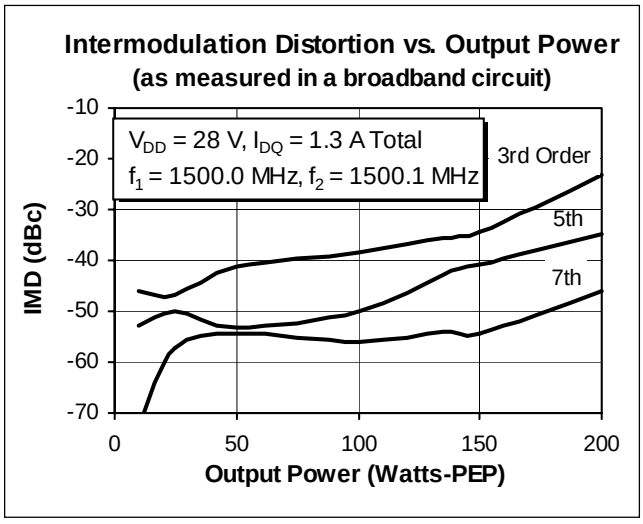
Typical Performance

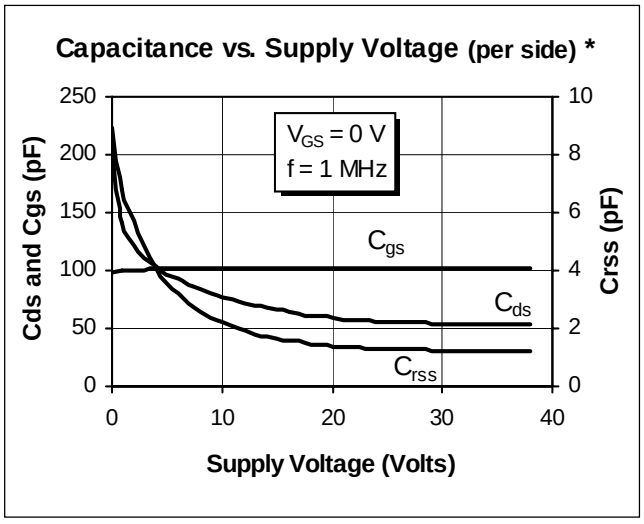




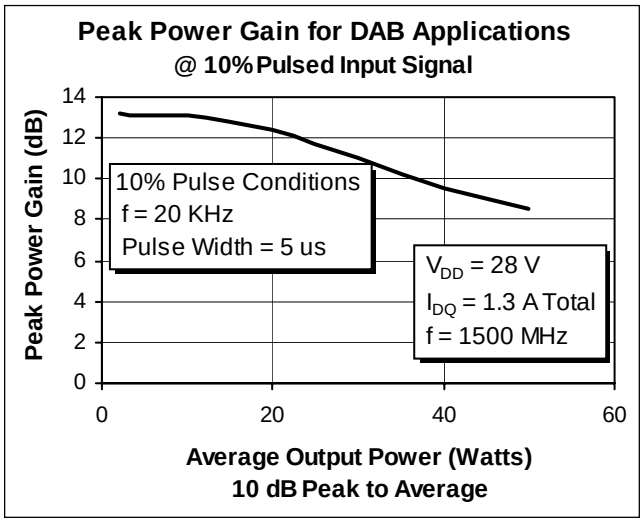


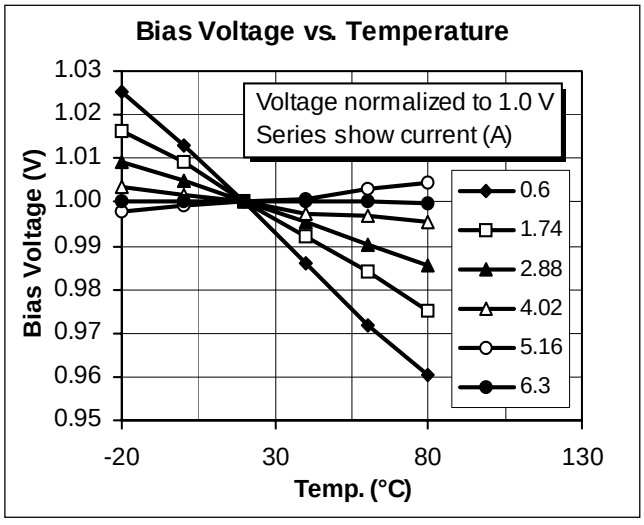






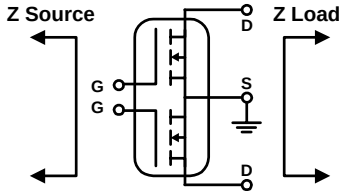
* This part is internally matched. Measurements of the finished product will not yield these results.



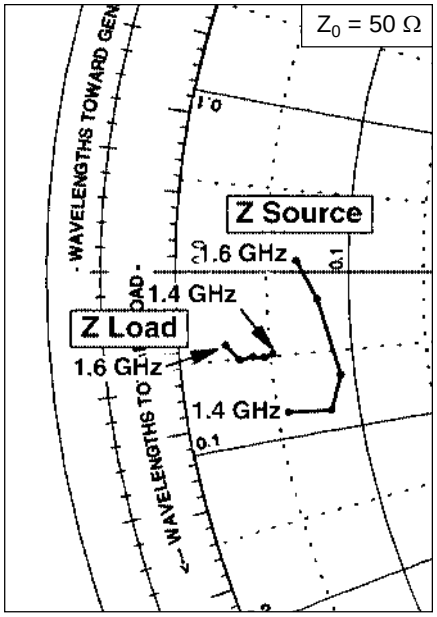


Impedance Data

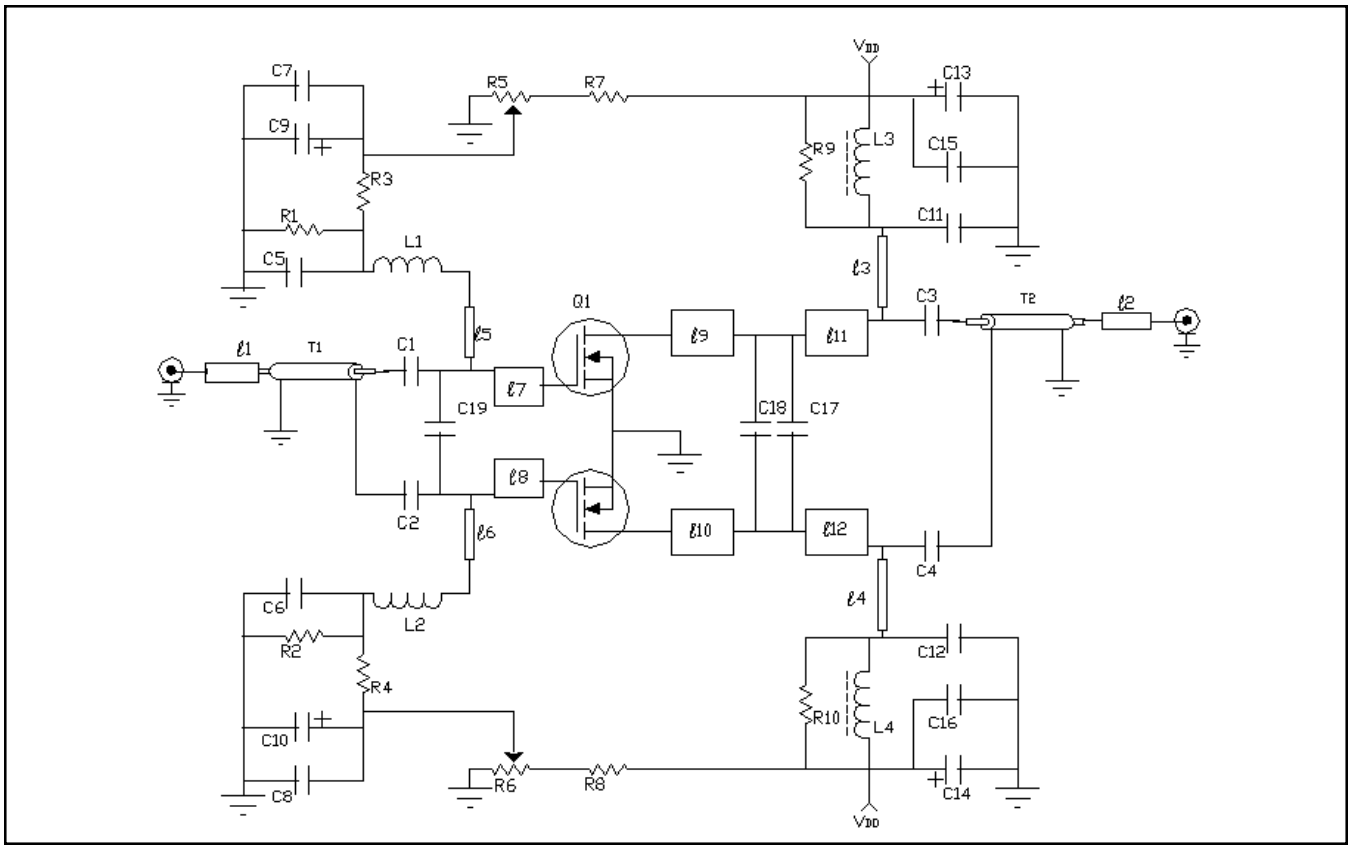
(V_{DD} = 28 V, P_{OUT} = 135 W,
I_{DQ} = 1.3 A Total)



Frequency	Z Source Ω		Z Load Ω	
GHz	R	jX	R	jX
1400	2.85	-4.23	2.60	-2.46
1450	4.16	-4.36	2.36	-2.53
1500	4.58	-3.30	2.04	-2.48
1550	4.02	-0.83	1.63	-2.52
1600	3.41	0.37	1.27	-2.08



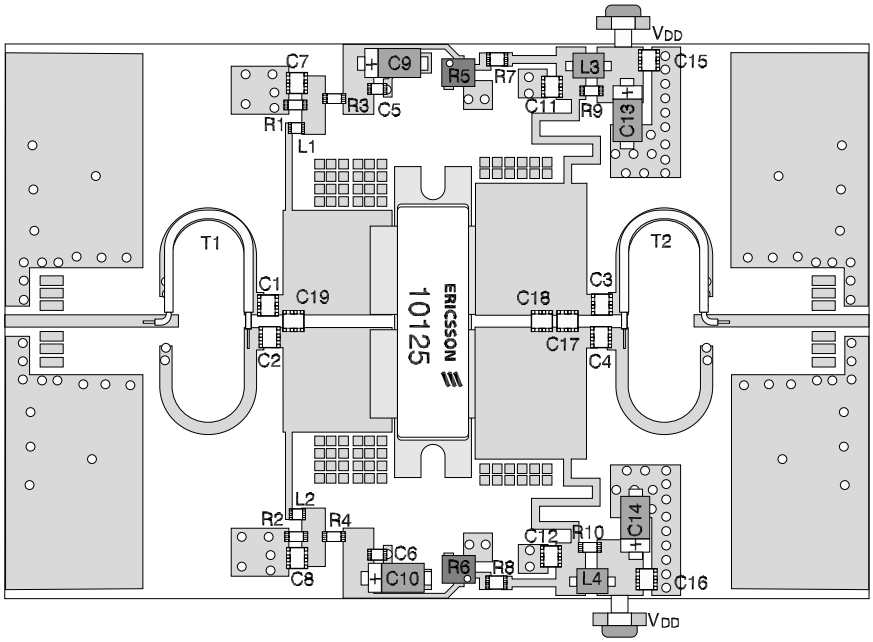
Test Circuit



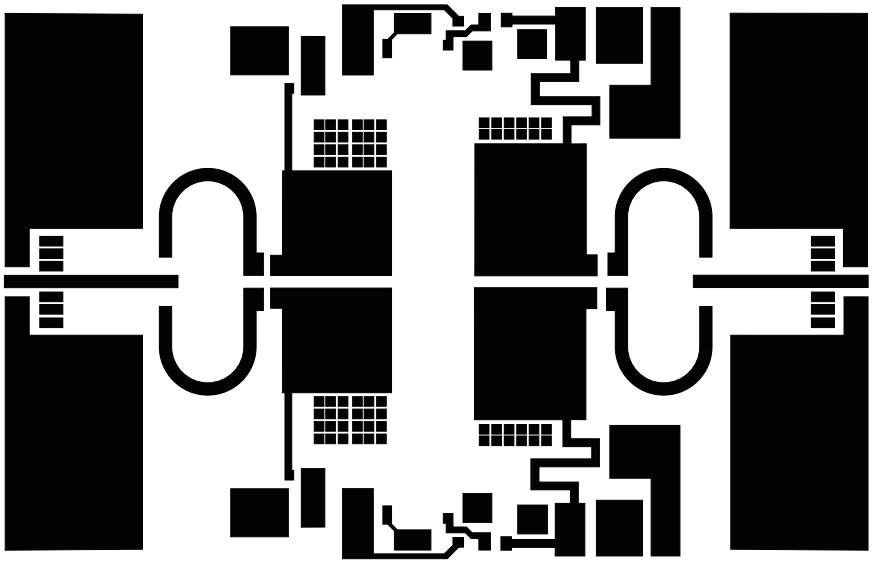
Test Circuit Block Diagram for f = 1.5 GHz

Q1	PTF 10125	LDMOS RF Transistor
ℓ1, ℓ2		Microstrip 50 Ω
ℓ3, ℓ4	.25 λ @ 1.5 GHz	Microstrip 70 Ω
ℓ5, ℓ6	.08 λ @ 1.5 GHz	Microstrip 80 Ω
ℓ7, ℓ8	.138 λ @ 1.5 GHz	Microstrip 9.5 Ω
ℓ9, ℓ10	.096 λ @ 1.5 GHz	Microstrip 7.7 Ω
ℓ11, ℓ12	.045 λ @ 1.5 GHz	Microstrip 7.7 Ω
C1, C2, C3, C4, C7, C8, C11, C12	13 pF Chip Cap	ATC 100 B
C5, C6, C15, C16	0.1 μF Chip Cap	K1206
C9, C10, C13, C14	10 μF SMT Tantalum Cap	
C17, C19	2.0 pF Chip Cap	ATC 100 B
C18	0.3 pF Chip Cap	ATC 100 B

L1, L2	2.7 nh SMT Coil	
L3, L4	4 mm SMT Ferrite Bead	
R1, R2, R3, R4	220 Ω Chip Resistor	K1206
R5, R6	2K SMT Potentiometer	
R7, R8	10 Ω Chip Resistor	K1206
R9, R10	1 Ω Chip Resistor	K1206
T1, T2	50 Ω Coaxial Balun	
Circuit Board	.031" thick, ε_r = 4.0, G200, AlliedSignal, 2 oz. copper	



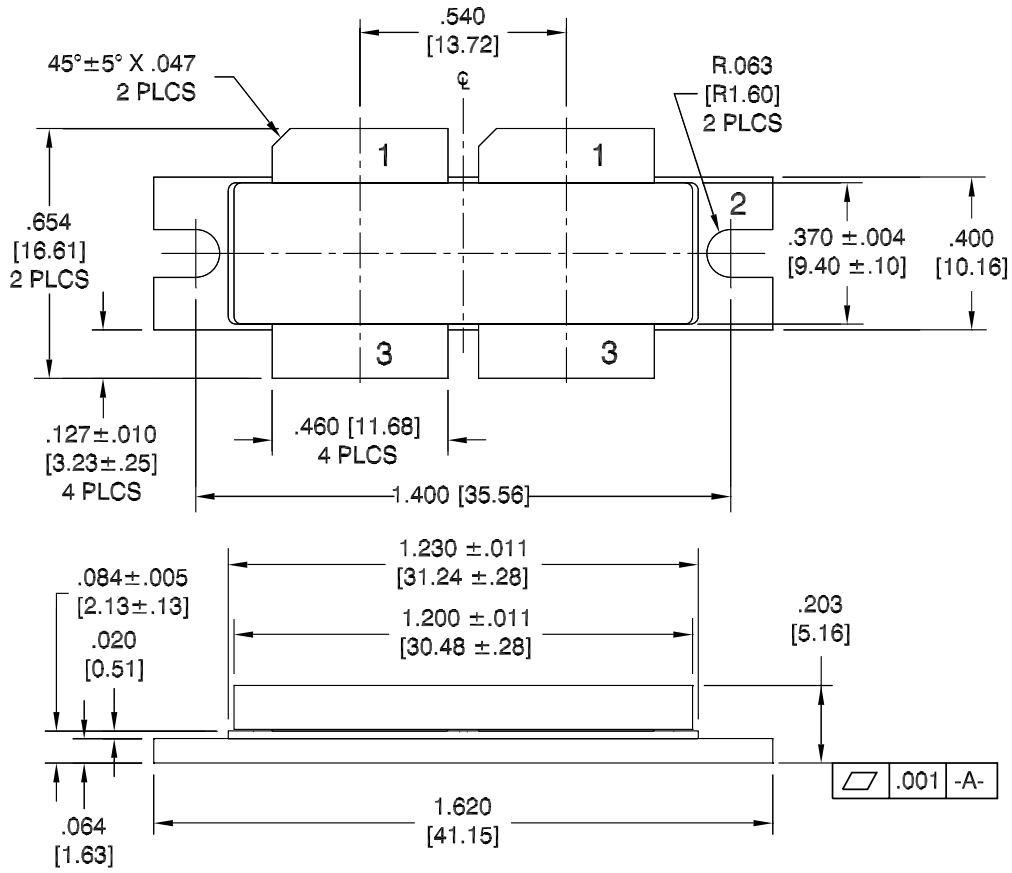
Parts Layout (not to scale)



Artwork (not to scale)

Case Outline Specifications

Package 20250



Unless otherwise specified
all tolerance ±.005" [0.13mm]

Pins: 1. Drain 2. Source 3. Gate
Lead Thickness: .004 +.002/-.001"
[0.10 +0.05/-0.03mm]

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